

## Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceed the OCM data sheet.

## Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-35835
  - Class Q Military
  - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)
  - Rochester is a critical supplier to DLA and meets all industry and DLA standards.

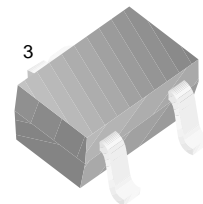
Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

# FJX2907A

FJX2907A

## General Purpose Transistor



1 SOT-323  
1. Base 2. Emitter 3. Collector

## PNP Epitaxial Silicon Transistor

### Absolute Maximum Ratings $T_a=25^\circ\text{C}$ unless otherwise noted

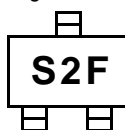
Symbol	Parameter	Value	Units
$V_{CBO}$	Collector-Base Voltage	-60	V
$V_{CES}$	Collector-Emitter Voltage	-60	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current	-600	mA
$P_C$	Collector Power Dissipation	350	mW
$T_{STG}$	Storage Temperature	150	$^\circ\text{C}$

### Electrical Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C = -10\mu\text{A}, I_E = 0$	-60		V
$BV_{CEO}$	* Collector-Emitter Breakdown Voltage	$I_C = -10\text{mA}, I_B = 0$	-60		V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_E = -10\mu\text{A}, I_C = 0$	-5		V
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = -50\text{V}, I_E = 0$		-0.01	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$V_{CE} = -10\text{V}, I_E = -0.1\text{mA}$ $V_{CE} = -10\text{V}, I_C = -1.0\text{mA}$ $V_{CE} = -10\text{V}, I_C = -10\text{mA}$ * $V_{CE} = -10\text{V}, I_C = -150\text{mA}$ * $V_{CE} = -10\text{V}, I_C = -500\text{mA}$	75 100 100 100 50	300	
$V_{CE(sat)}$	* Collector-Emitter Saturation Voltage	$I_C = -150\text{mA}, I_B = -15\text{mA}$ $I_C = -500\text{mA}, I_B = -50\text{mA}$		-0.4 -1.6	V V
$V_{BE(sat)}$	* Base-Emitter Saturation Voltage	$I_C = -150\text{mA}, I_B = -15\text{mA}$ $I_C = -500\text{mA}, I_B = -50\text{mA}$		-1.3 -2.6	V V
$f_T$	Current Gain Bandwidth Product	$I_C = -50\text{mA}, V_{CE} = -20\text{V}$ , $f = 100\text{MHz}$	200		MHz
$C_{ob}$	Output Capacitance	$V_{CB} = -10\text{V}, I_E = 0$ $f = 1.0\text{MHz}$		8	pF
$t_{ON}$	Turn On Time	$V_{CC} = -30\text{V}, I_C = -150\text{mA}$ $I_{B1} = -15\text{mA}$		45	ns
$t_{OFF}$	Turn Off Time	$V_{CC} = -6\text{V}, I_C = -150\text{mA}$ $I_{B1} = I_{B2} = 15\text{mA}$		100	ns

\* Pulse Test:  $PW \leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$

### Marking



# Typical Characteristics

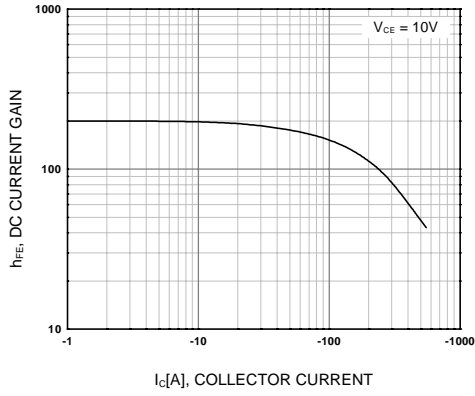


Figure 1. DC current Gain

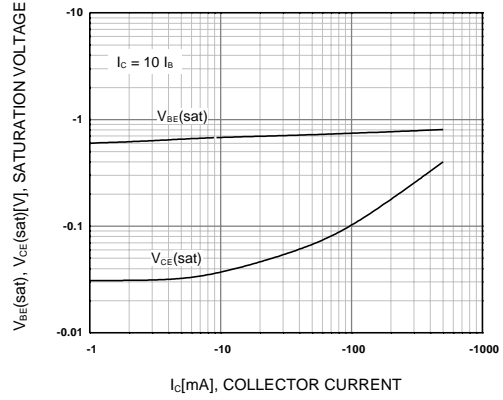


Figure 2. Collector-Emitter Saturation Voltage  
Base-Emitter Saturation Voltage

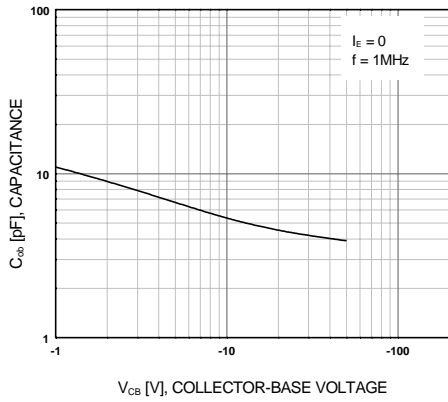


Figure 3. Output Capacitance

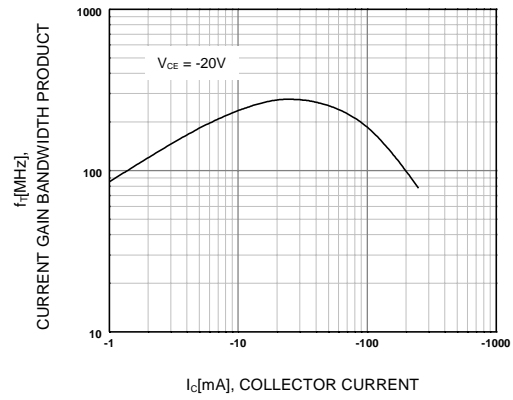
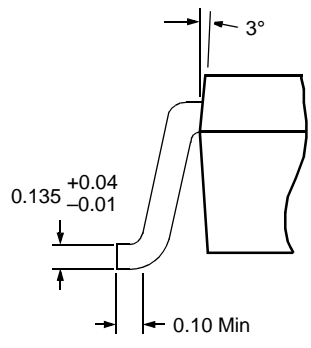
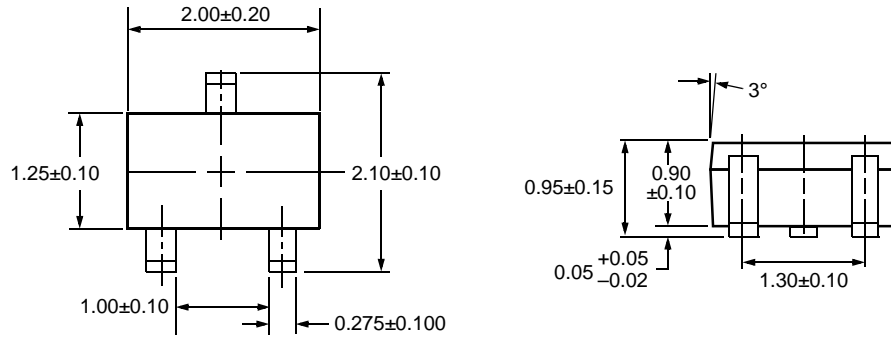


Figure 4. Current Gain Bandwidth Product

# Package Dimensions

FJX2907A

## SOT-323



Dimensions in Millimeters

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## PRODUCT STATUS DEFINITIONS

### Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

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PNP Epitaxial Silicon Transistor

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Features

**General Purpose Transistor**

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Product	Product status	Pricing*	Package type	Leads	Packing method
FJX2907ATF	Full Production	\$0.068	SOT-323	3	TAPE REEL

\* 1,000 piece Budgetary Pricing

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